# P-Channel 60-V (D-S) MOSFET

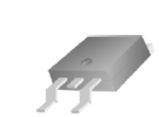
#### **Key Features:**

- Low r<sub>DS(on)</sub> trench technology
- · Low thermal impedance
- · Fast switching speed

#### **Typical Applications:**

- PoE Power Sourcing Equipment
- PoE Powered Devices
- Telecom DC/DC converters
- White LED boost converters





VDS (V)

-60

**PRODUCT SUMMARY** 

 $r_{DS(on)}(m\overline{\Omega})$ 

17 @ V<sub>GS</sub> = -10V

23 @ V<sub>GS</sub> = -4.5V



ID(A)

-44

-38

ABSOLUTE MAXIMUM RATINGS ( $T_A = 25^{\circ}C$ UNLESS OTHERWISE NOTED)					
Parameter		Symbol	Limit	Units	
Drain-Source Voltage		V <sub>DS</sub>	-60	V	
Gate-Source Voltage		V <sub>GS</sub>	±20	v	
Continuous Drain Current	T <sub>C</sub> =25°C	I <sub>D</sub>	-44	А	
Pulsed Drain Current <sup>b</sup>		I <sub>DM</sub>	-150	A	
Continuous Source Current (Diode Conduction)		ا <sub>S</sub>	-48	А	
Power Dissipation	T <sub>C</sub> =25°C	PD	50	W	
Operating Junction and Storage Temperature Range		T <sub>J</sub> , T <sub>stg</sub>	-55 to 175	°C	

THERMAL RESISTANCE RATINGS				
Parameter	Symbol	Maximum	Units	
Maximum Junction-to-Ambient <sup>a</sup>	R <sub>θJA</sub>	40	°C/W	
Maximum Junction-to-Case	$R_{ extsf{ heta}JC}$	3	C/ VV	

Notes

- a. Surface Mounted on 1" x 1" FR4 Board, drain pad using 2 oz copper, value dependent on PC board thermal characteristics
- b. Pulse width limited by maximum junction temperature

## **Typical Electrical Characteristics**

Parameter	Symbol	Test Conditions	Min	Тур	Max	Unit	
Static							
Gate-Source Threshold Voltage	V <sub>GS(th)</sub>	$V_{DS} = V_{GS}$ , ID = -250 uA	-1			V	
Gate-Body Leakage	I <sub>GSS</sub>	$V_{DS} = 0 \text{ V}, \text{ V}_{GS} = \pm 20 \text{ V}$			±100	nA	
Zero Gate Voltage Drain Current		$V_{DS} = -48 \text{ V}, \text{ V}_{GS} = 0 \text{ V}$		-1			
	DSS	$V_{DS} = -48 \text{ V}, V_{GS} = 0 \text{ V}, T_{J} = 55^{\circ}\text{C}$			-10	– uA	
On-State Drain Current	I <sub>D(on)</sub>	$V_{DS} = -5 V, V_{GS} = -10 V$	-20			А	
Drain Source On Registence	r	$V_{GS} = -10 \text{ V}, \text{ I}_{D} = -22 \text{ A}$			17	mΩ	
Drain-Source On-Resistance	r <sub>DS(on)</sub>	$V_{GS} = -4.5 \text{ V}, \text{ I}_{D} = -22 \text{ A}$			23	11152	
Forward Transconductance	<b>g</b> <sub>fs</sub>	$V_{DS} = -15 \text{ V}, \text{ I}_{D} = -22 \text{ A}$		8		S	
Diode Forward Voltage	V <sub>SD</sub>	$I_{S} = -24 \text{ A}, V_{GS} = 0 \text{ V}$		-0.9		V	
Dynamic							
Total Gate Charge	Qg			83		nC	
Gate-Source Charge	$Q_gs$	$V_{\text{DS}}$ = -30 V, $V_{\text{GS}}$ = -10 V, $I_{\text{D}}$ = -22 A		18			
Gate-Drain Charge	Q <sub>gd</sub>			20			
Turn-On Delay Time	t <sub>d(on)</sub>			11			
Rise Time	t <sub>r</sub>	$V_{DD}$ = -30 V, $R_L$ = 1.4 $\Omega$ , $I_D$ = -22 A,		16		nS	
Turn-Off Delay Time	t <sub>d(off)</sub>	$V_{GEN}$ = -10 V, $R_{GEN}$ = 6 $\Omega$		113			
Fall Time	t <sub>f</sub>			42			
Input Capacitance	C <sub>iss</sub>			4654			
Output Capacitance	C <sub>oss</sub>	$V_{DS}$ = -15 V, $V_{GS}$ = 0 V, f =1 MHz		526		pF	
Reverse Transfer Capacitance	C <sub>rss</sub>			347			

Notes

- a. Pulse test: PW <= 300us duty cycle <= 2%.
- b. Guaranteed by design, not subject to production testing.

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4

0.9

10

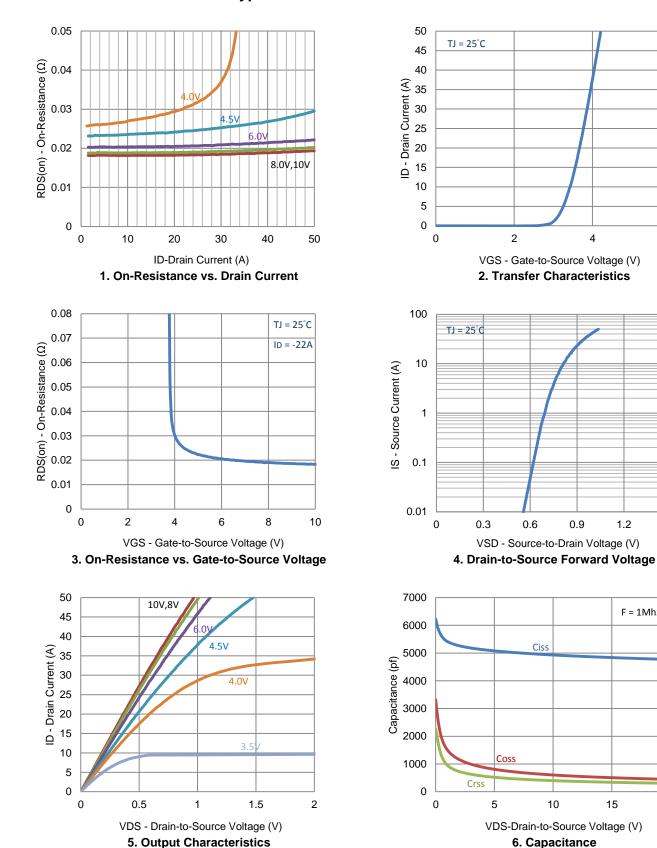
1.2

F = 1Mhz

1.5

20

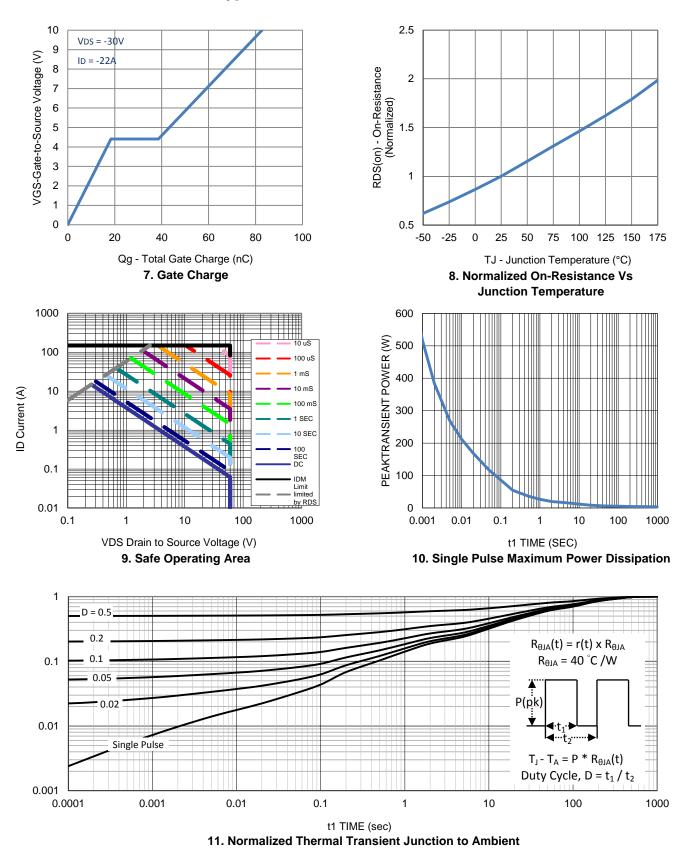
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#### **Typical Electrical Characteristics**

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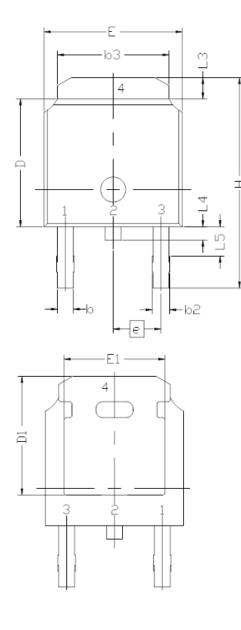
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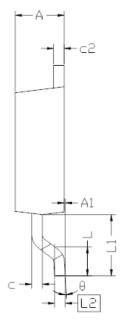


#### **Typical Electrical Characteristics**

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### **Package Information**





	DIVENO		SEGUTO
SYMBOL	DIMENS:	IUNAL I I NOM	
0111202	MIN		MAX
E	6.40	6,60	6.731
L	1.40	1.52	1.77
L1		.743 RI	
L2	0.	.508 BS	C O
L3	0.89		1.27
L4	0.64		1.01
L5			
D	6.00	6.10	6,223
Н	9.40	10.00	10.40
b	0.64	0.76	0.88
b2	0.77	0.84	1.14
b3	5.21	5.34	5.46
e	2.286 BSC		
A	2.20	2.30	2.38
A1	0		0.127
C	0.45	0.50	0.60
c2	0.45	0.50	0.58
D1	5.30		
E1	4.40		
θ	0°		10*

#### Note:

- 1. All Dimension Are In mm.
- 2. Package Body Sizes Exclude Mold Flash, Protrusion Or Gate Burrs. Mold Flash, Protrusion Or Gate Burrs Shall Not Exceed 0.10 mm Per Side.
- 3. Package Body Sizes Determined At The Outermost Extremes Of The Plastic Body Exclusive Of Mold Flash, Gate Burrs And Interlead Flash, But Including Any Mismatch Between The Top And Bottom Of The Plastic Body.